

NOT RECOMMENDED FOR NEW DESIGN **USE DMN3110S**



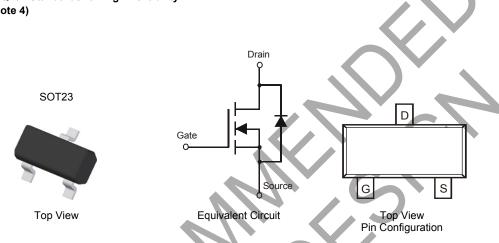
N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance:
 - 57mΩ @ V_{GS} = 10V
 - 112mΩ @ V_{GS} = 4.5V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- **PPAP** Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Ordering Information (Note 5)

Part Number	Qualification	Case	Packaging
DMN3112S-7	Standard	SOT23	3000/Tape & Reel
DMN3112SQ-7	Automotive	SOT23	3000/Tape & Reel

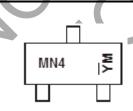
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. Notes:

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- <1000ppm antimony compounds. 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



MN4	MX	

MN4 = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) embly/ Test site)

Chengdu A/T Site

Shanghai A/T Site

Date Code Key

24.0 0040.00												
Year	2008	2009	20	10	2011	2012	2013	2014	20	15	2016	2017
Code	V	W	>	(Y	Z	А	В	(C	D	E
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V _{DSS}	30	V
Gate-Source Voltage		V _{GSS}	±20	V
Drain Current (Note 6)	T _A = +25°C T _A = +70°C	ID	5.8 4.2	А
Drain Current (Note 6)	Pulsed	I _{DM}	20	A
Body-Diode Continuous Current (Note 6)		Is	2.0	A

Thermal Characteristics

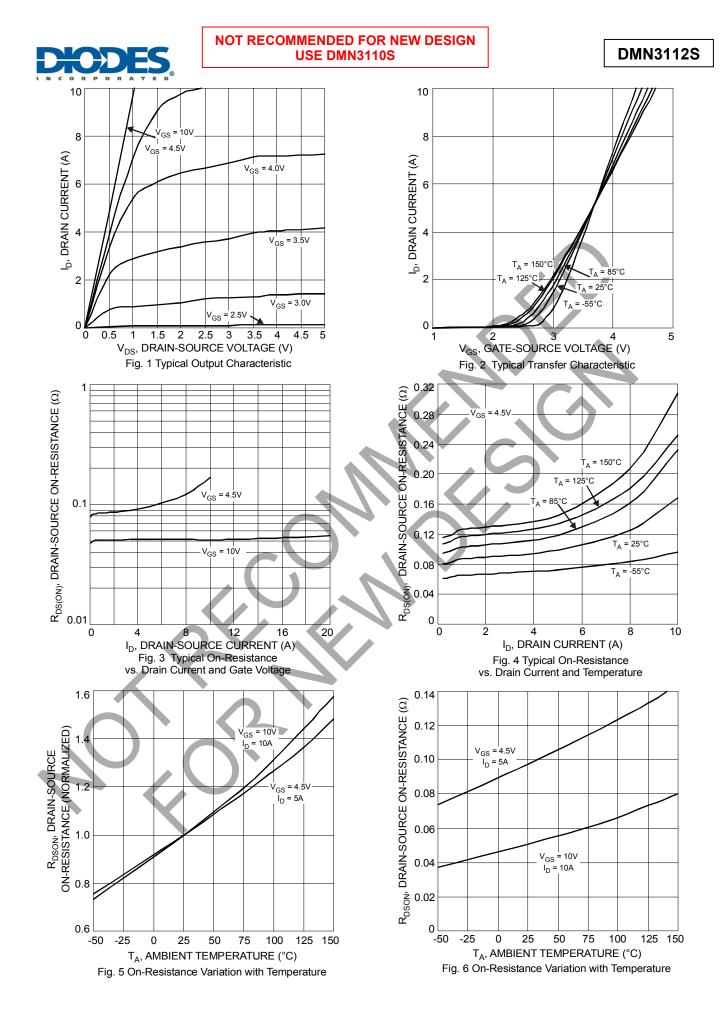
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	PD	1.4	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 6)	R ₀ JA	90	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

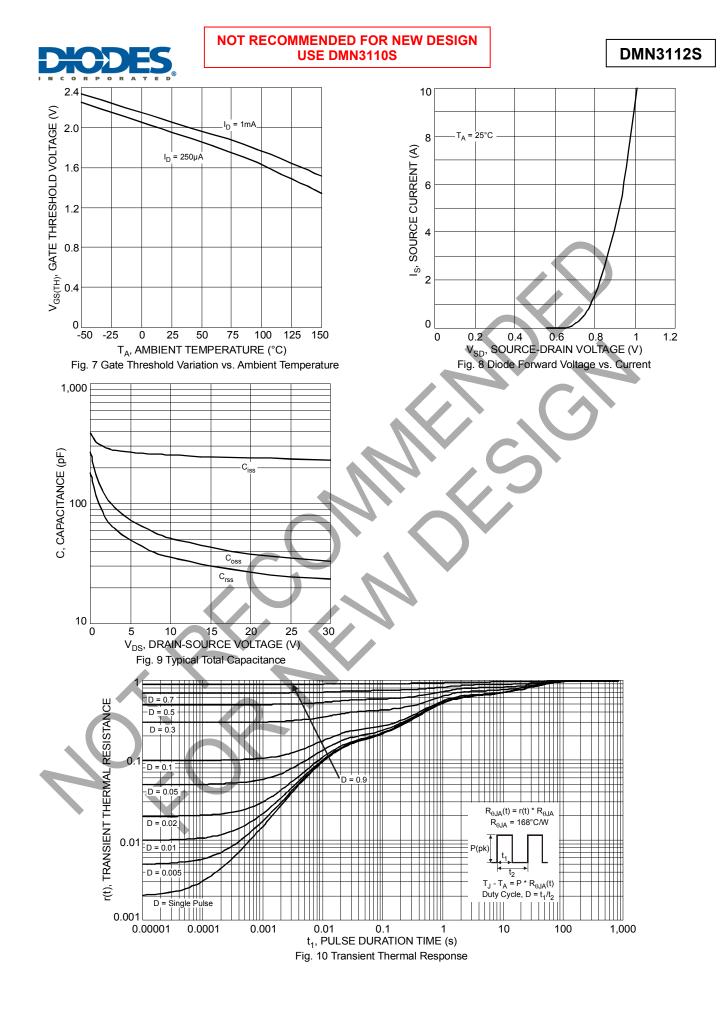
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

		10 100 100				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30		-	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	IDSS	· - ·		800	nA	V _{DS} = 30V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}			±80 ±800	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$ $V_{GS} = \pm 25V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1.3	1.9	2.2	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	R _{DS (ON)}	_	47 92	57 112	mΩ	V _{GS} = 10V, I _D = 5.8A V _{GS} = 4.5V, I _D = 4.2A
Forward Transconductance	Y _{fs}		4.7	_	S	V _{DS} = 5V, I _D = 4.2A
Source-Drain Diode Forward Voltage	V _{SD}	—	0.78	1.1	V	V _{GS} = 0V, I _S = 2.0A
DYNAMIC CHARACTERISTICS (Note 8)		/				
Input Capacitance	Ciss	_	268		pF	
Output Capacitance	Coss	_	73	_	pF	V _{DS} = 5V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	50	_	pF	

Notes:

6. Device mounted on FR-4 PCB. t ≤5 sec.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

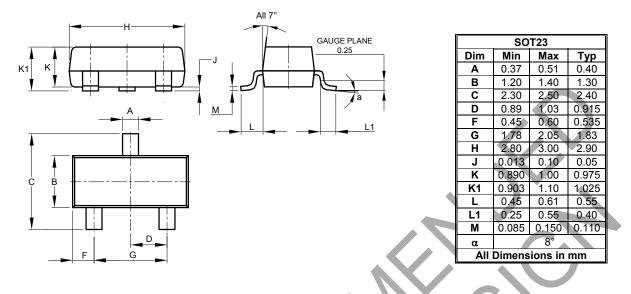






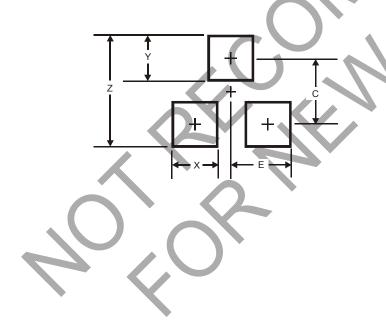
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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